

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|---|---|------------------|---------|---------------------|
| L1 | 1253 | 117/90,94,104.ccls. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:02 |
| L2 | 2 | "thermal radiation absorption layer" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:02 |
| L3 | 907 | "TEOS oxide layer" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:03 |
| L4 | 117412 | "SiC" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:04 |
| L5 | 1022 | "highly doped silicon" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:04 |
| L6 | 0 | l4 near l5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:05 |
| L7 | 118894 | l4 samr l5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:05 |

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|-----|-------|---|---|----|-----|---------------------|
| L8 | 7 | I4 same I5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:05 |
| L9 | 0 | I1 and I5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:06 |
| L10 | 2 | I3 and I5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:06 |
| L11 | 63 | I4 and I5 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/13 18:06 |
| S1 | 2 | "20020028314" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:18 |
| S2 | 9 | "6447604" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/16 09:46 |
| S3 | 27 | "5771110" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/16 09:47 |
| S4 | 11 | "1143047" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/16 09:48 |
| S5 | 19 | "447047" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/16 09:47 |
| S6 | 12 | "1143047" | US-PGPUB; USPAT; USOCR; EPO; DERWENT | OR | OFF | 2006/03/16 09:48 |
| S7 | 94588 | "silicon carbide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2006/03/16 09:55 |
| S8 | 2 | "thermal radiation absorption layer" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2006/03/16 09:55 |

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| S9 | 1 | S7 and S8 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2006/03/16 09:56 |
| S10 | 96 | "radiation absorption layer" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2006/03/16 09:56 |
| S11 | 3 | S7 and S10 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2006/03/16 11:08 |
| S12 | 1 | "1184897" | EPO | OR | OFF | 2006/03/16 11:09 |
| S13 | 1 | "1280190" | EPO | OR | OFF | 2006/03/16 11:08 |
| S14 | 7 | "6214108" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 13:43 |
| S15 | 2 | "6824610" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 13:43 |
| S16 | 226 | 117/94.ccls. | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:19 |
| S17 | 233 | 117/90.ccls. | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:19 |
| S18 | 16 | "thermal absorption layer" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:19 |
| S19 | 0 | S16 and S18 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:19 |
| S20 | 0 | S17 and S18 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:28 |
| S21 | 2842 | "MOVPE" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 21:28 |
| S22 | 0 | S18 and S21 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:13 |
| S23 | 372 | 117/104.ccls. | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:13 |
| S24 | 0 | S18 and S23 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:13 |

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| S25 | 8509 | "absorption layer" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:13 |
| S26 | 0 | S23 and S25 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:14 |
| S27 | 1627 | "radiation layer" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:14 |
| S28 | 0 | S23 and S27 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:14 |
| S29 | 25093 | "TEOS" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:14 |
| S30 | 663 | "TEOS oxide layer" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:15 |
| S31 | 0 | S23 and S30 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:15 |
| S32 | 0 | S21 and S30 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:15 |
| S33 | 84932 | "siC" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:48 |
| S34 | 84932 | "SiC" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:48 |
| S35 | 2842 | "movpe" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:48 |
| S36 | 741 | S34 and S35 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:48 |
| S37 | 67689 | "backside" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:48 |
| S38 | 39 | S36 and S37 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:49 |
| S39 | 105914 | "polysilicon" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:49 |
| S40 | 0 | S38 and S39 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:49 |

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| S41 | 878176 | "silicon" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:49 |
| S42 | 21590 | "doped silicon" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:49 |
| S43 | 2 | S38 and S42 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:58 |
| S44 | 832 | "AlGaInN" | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:58 |
| S45 | 4 | S34 near S44 | US-PGPUB; USPAT; USOCR; DERWENT | OR | OFF | 2006/03/17 22:58 |
| S46 | 8788391 | TW "447047" A | EPO; JPO | OR | OFF | 2006/03/18 15:29 |
| S47 | 1 | "447047" | EPO; JPO | OR | OFF | 2006/03/18 15:29 |
| S48 | 5 | "447047" | DERWENT | OR | OFF | 2006/03/18 17:37 |
| S49 | 1 | "6927155" | DERWENT | OR | OFF | 2006/03/18 17:39 |
| S50 | 2 | "6730939" | USPAT; DERWENT | OR | OFF | 2006/03/18 17:38 |
| S51 | 2 | "6927155" | USPAT; DERWENT | OR | OFF | 2006/03/18 17:39 |
| S52 | 73863 | "non-metallic" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 17:40 |
| S53 | 84385 | "backside" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 17:40 |
| S54 | 872 | S52 and S53 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 17:40 |
| S55 | 101952 | "silicon carbide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2007/01/23 17:40 |

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| S56 | 65 | S54 and S55 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:19 |
| S57 | 109 | "radiation absorption layer" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2007/01/23 17:41 |
| S58 | 0 | S56 and S57 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 17:41 |
| S59 | 84385 | "backside" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:19 |
| S60 | 3388 | "SiC Substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:19 |
| S61 | 11 | S59 near S60 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:40 |
| S62 | 2237658 | "substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:40 |
| S63 | 18899 | "underlayer" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:40 |
| S64 | 1587 | S62 near S63 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:40 |

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| S65 | 102070 | "silicon carbide" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/01/23 18:41 |
| S66 | 977 | "highly doped silicon" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/18 18:39 |
| S67 | 3908 | "SiC substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/18 18:40 |
| S68 | 2 | "thermal radiation absorption layer" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/18 18:40 |
| S69 | 0 | S66 near S67 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/18 18:40 |
| S70 | 0 | S66 same S67 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/18 18:40 |
| S71 | 5 | S66 and S67 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:33 |
| S72 | 1042 | "highly doped polysilicon" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:41 |

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| S73 | 0 | "under the substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:34 |
| S74 | 4041 | "substrate underlying" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:34 |
| S75 | 0 | S72 near S74 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:34 |
| S76 | 1 | S72 same S74 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:34 |
| S77 | 8 | S72 and S74 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 11:34 |
| S78 | 0 | "highly doped polysilicone" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:02 |
| S79 | 12 | "1143047" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S80 | 2866 | "rear side substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |

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| S81 | 268997 | "rear side" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S82 | 2428803 | "substrate" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S83 | 1904 | "polysilicone" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S84 | 3276 | S81 near S82 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S85 | 0 | S83 near S84 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S86 | 0 | S83 and S84 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S87 | 8 | S83 same "116" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:03 |
| S88 | 0 | S83 same S84 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:04 |

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| S89 | 0 | S83 and S84 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:08 |
| S90 | 5 | "highly doped silicone" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:08 |
| S91 | 0 | S83 and S90 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/12/20 12:08 |

5/ 13/ 2008 6:06:38 PM

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